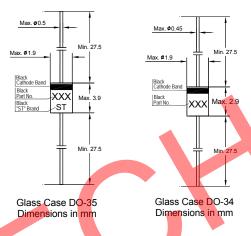
#### Silicon Epitaxial Planar Switching Diode

#### **Applications**

· High-speed switching

This diode is also available in MiniMELF case with the type designation LL4148



### Absolute Maximum Ratings (T<sub>a</sub> = 25°C)

| Parameter  | Symbol             | Value              | Unit |
|--|--------------------|--------------------|------|
| Peak Reverse Voltage   | $V_{RM}$           | 100                | V    |
| Reverse Voltage  | $V_R$              | 75                 | V    |
| Average Rectified Forward Current  | I <sub>F(AV)</sub> | 200                | mA   |
| Non-repetitive Peak Forward Surge Current at t = 1 s at t = 1 ms at t = 1 µs | I <sub>FSM</sub>   | 0.5<br>1<br>4      | А    |
| Power Dissipation  | P <sub>tot</sub>   | 500 <sup>1)</sup>  | mW   |
| Junction Temperature   | T <sub>j</sub>     | T <sub>j</sub> 200 |      |
| Storage Temperature Range  | T <sub>stg</sub>   | - 65 to + 200      | °C   |

<sup>1)</sup> Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature.

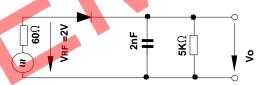




### Characteristics at $T_a = 25^{\circ}C$

| Parameter  | Symbol                                   | Min.        | Max.               | Unit           |
|--|--|-------------|--------------------|----------------|
| Reverse Breakdown Voltage at $I_R$ = 100 $\mu$ A at $I_R$ = 5 $\mu$ A  | V <sub>(BR)R</sub><br>V <sub>(BR)R</sub> | 100<br>75   | -                  | V              |
| Forward Voltage<br>at I <sub>F</sub> = 10 mA   | V <sub>F</sub>                           | -           | 1                  | V              |
| Leakage Current<br>at $V_R$ = 20 V<br>at $V_R$ = 75 V<br>at $V_R$ = 20 V, $T_j$ = 150°C                          | <sub>R</sub>                             | -<br>-<br>- | 25<br>5<br>50      | nΑ<br>μΑ<br>μΑ |
| Capacitance at V <sub>R</sub> = 0, f = 1 MHz   | C <sub>tot</sub>                         | -           | 4                  | pF             |
| Voltage Rise when Switching ON tested with 50 mA Forward Pulses tp = 0.1 s, Rise Time < 30 ns, fp = 5 to 100 KHz | V <sub>fr</sub>                          | -           | 2.5                | V              |
| Reverse Recovery Time at $I_F$ = 10 mA to $I_R$ = 1 mA, Irr = 0.1 x $I_{R_s}$ $V_R$ = 6 V, $R_L$ = 100 $\Omega$  | t <sub>rr</sub>                          | -           | 4                  | ns             |
| Thermal Resistance Junction to Ambient Air   | R <sub>thA</sub>                         | -           | 0.35 <sup>1)</sup> | K/mW           |
| Rectification Efficiency at f = 100 MHz, V <sub>RF</sub> = 2 V   | ην                                       | 0.45        | -                  | -              |

<sup>1)</sup> Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature.



**Rectification Efficiency Measurement Circuit** 



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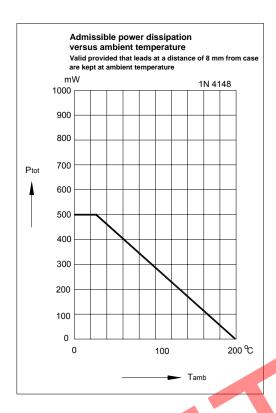


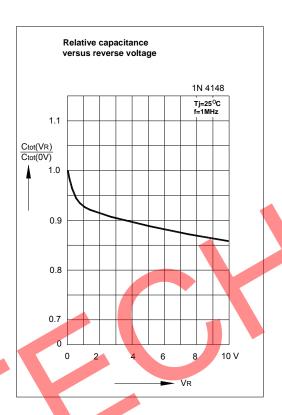


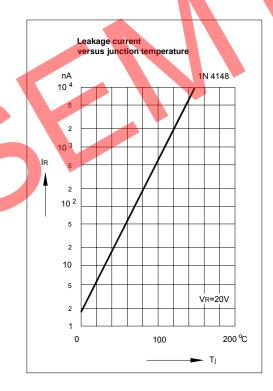


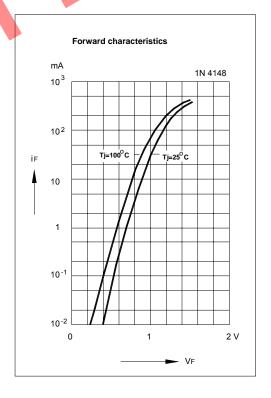














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